

EE561- PCB Design of closed loop operation of Boost converter

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1 Objective

Aim- Realize a closed loop control of boost converter controlled by analogue PI controller. The specifications for boost converter are given below : Input voltage $V_{in}=96v$ $V_o=200v$ $f_{sw}=20kHz$ output voltage ripple= 10% Inductor current ripple=20% $P_o=500w$

2 Calculations

1. Output Current, Input Current:

$$P_o = \frac{V_o^2}{R}$$

$$R = \frac{200^2}{500} = 80\Omega$$

$$I_o = I_{min} = \frac{P_o}{V_o} = \frac{500}{200} = 2.5\text{amps} \quad I_{in} = \frac{P_o}{V_{in}} = \frac{500}{96} = 5.21\text{amps}$$

2. Duty Ratio:

$$V_o = \frac{V_{in}}{1-D}$$

$$200 = \frac{96}{1-D}$$

$$D = 0.52$$

3. Inductance:

$$L = \frac{DV_s}{\Delta I_L * f_s} \quad \text{but ; } \frac{\Delta I_L}{I_L} = 0.2$$

$$\text{also, } I_s = I_L = \frac{I_o}{1-D}$$

$$\text{therefore, } L = \frac{0.52 * 96(1 - 0.52)}{20 * 10^3 * 0.2 * 2.5} = 2.396\text{mh}$$

4. Capacitance:

$$C = \frac{D * I_o}{\Delta V_o * f} \quad \text{but ; } \frac{\Delta V_o}{V_o} = 0.1$$

$$\text{therefore, } C = \frac{0.52 * 2.5}{0.1 * 200 * 20 * 10^3} = 3.25\mu F$$

5. Mosfet rating:

$$V_{ds} = V_d + V_o$$

$$\text{Thus, } V_{ds} \approx 200V$$

$$I_d = D * I_{in} = 0.52 * 5.21 \approx 2.7Amp$$

6. Diode:

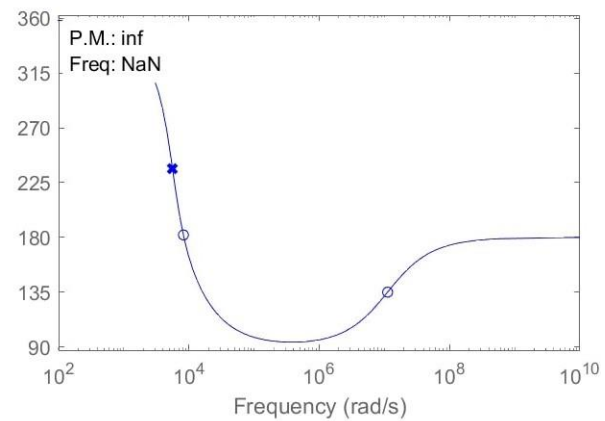
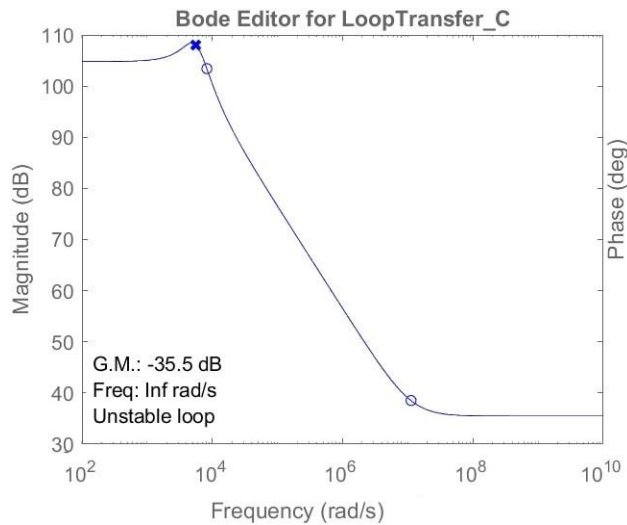
$$V_{RBmax} \approx 200V$$

$$I_d = I_o = 2.5Amp$$

3 Controller Design

3.1 Transfer function

$$\frac{V_o(S)}{D(S)} = \frac{-1.88 * 10^{-6}s^2 - 21.05s + 1.73 * 10^5}{3.155 * 10^{-8}s^2 + 0.000146s + 1}$$



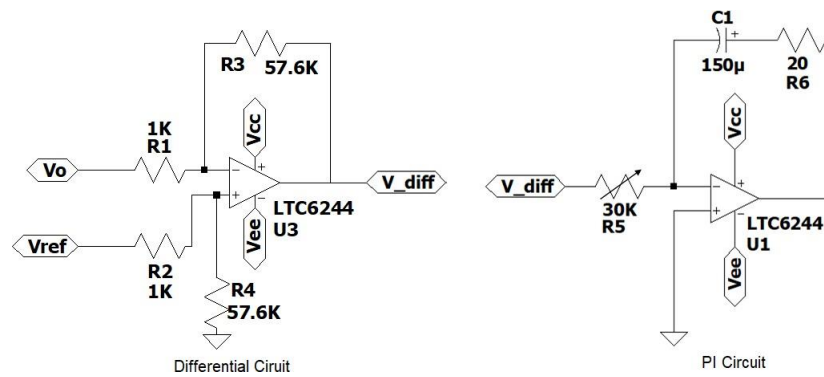
3.2 PI controller

Gain cross-over frequency was found out to be 1.02 kHz. The corresponding PI values were derived using SISO tool.

$$K_p \approx 0.0012, K_i \approx 0.3$$

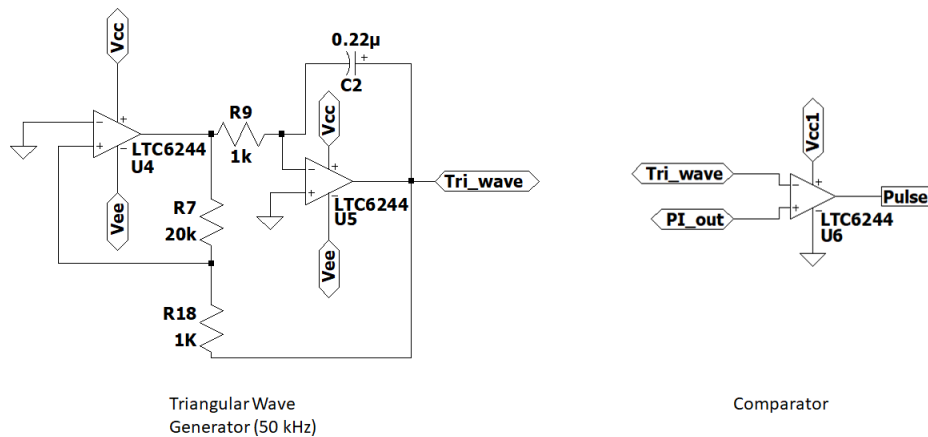
3.2.1 Differential and PI controller

$$V_{CC} = 10V, V_{EE} = -10V$$



3.2.2 Triangular Wave Generator and comparator

The output of PI controller is reversed and compared with a triangular wave to generate gate drive signals.



4 Components Selection

Component	Manufacturer ID	Description	Quantity
MOSFET	TK4A60D	$V_{ds}=600V$, $I_d=4amp$	1
Diode	QH03TZ600	$V_{rrm}=600V$, $I_f=3amp$	1
Resistor	1712-HCH335J82RJ-ND	$R=82ohm$, wire wound , $P_{rating}=500W$	1
Opamp	NJM2122D	Slew rate= $2.4V/us$, Supply voltage= $\pm(10)V$	4
Capacitor	200LLE3RMEFC6.3X11	$C=3.3uf$, V rated= $200V$	1
Rheostat	3362P-1-103LF	$R=10 kohm$ and $30 kohm$, $P=0.5W$	2
Inductor	SS28V-25045-CH	$L=4.5 mh$, $I=2.5amp$, $R=160 mohm$	2

5 Spice Model

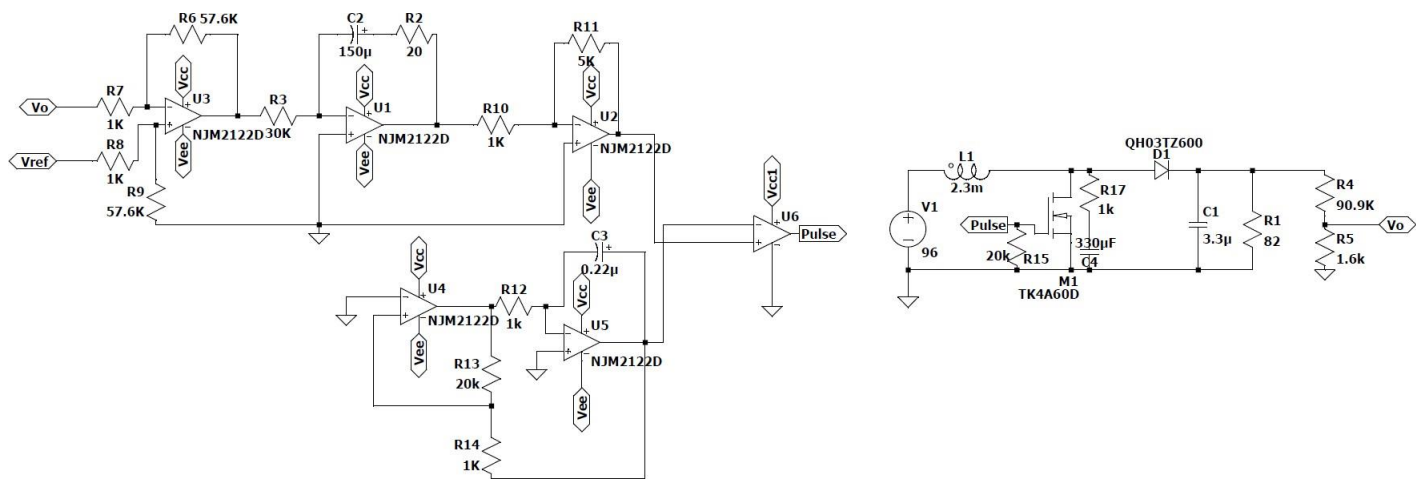


Figure 1: SPICE MODEL

6 PCB Model

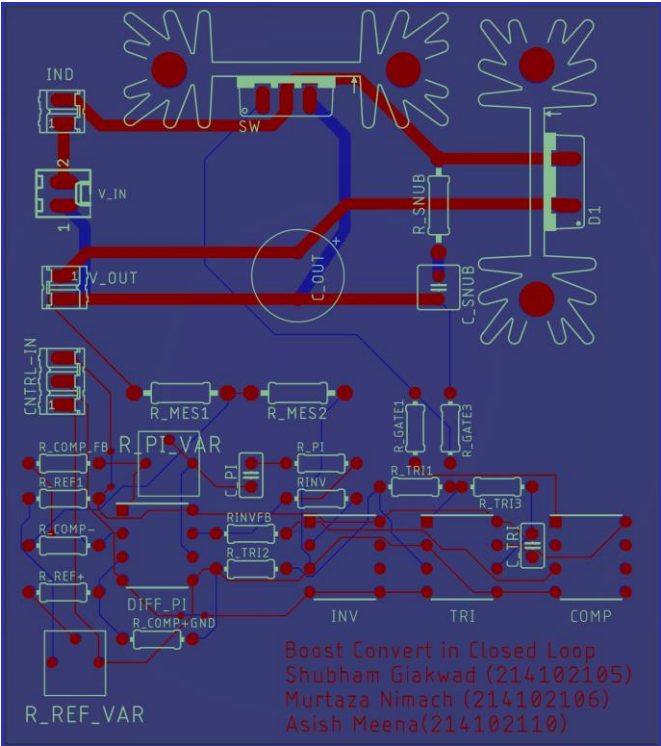


Figure 2: PCB MODEL